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#9/24/A  
V Brown  
1-3003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Setsuo NAKAJIMA et al.      Art Unit : 2812  
Serial No. : 09/768,618      Examiner : Stanetta Isaac  
Filed : January 25, 2001  
Title : SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD

Commissioner for Patents  
Washington, D.C. 20231

RESPONSE

In response to the action mailed August 22, 2002, please amend the application as follows:

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In the claims:

**Please amend claims 13 and 20-24 as follows:**

a1

-- 13. (Amended) A method of manufacturing a semiconductor device comprising:

- ✓ forming a heat absorbing layer in an island form over a substrate;
- ✓ forming an insulating film over said heat absorbing layer;
- ✓ forming a non-single crystalline semiconductor film on said insulating film;
- ✓ irradiating said non-single crystalline semiconductor film with light so that said semiconductor film is melted and solidified; and
- ✓ patterning said semiconductor film into a semiconductor island, the semiconductor island not overlapping with the heat absorbing layer,

wherein a channel length direction of the semiconductor island is parallel to a longitudinal outer edge of said heat absorbing layer.

a2

20. (Amended) A method of manufacturing a semiconductor device comprising:

- forming a heat absorbing layer comprising a metal over a substrate;
- forming a first insulating film over said heat absorbing layer;
- forming a non-single crystalline semiconductor film on said first insulating film;